

L Number	Hits	Search Text	DB	Time stamp
1	4241	magnetoresistive and resistance	USPAT; EPO; JPO; DERWENT; USOCR	2002/12/04 13:07
2	168	((magnetoresistive and resistance) and RAM	USPAT; EPO; JPO; DERWENT; USOCR	2002/12/04 13:07
4	16	((((magnetoresistive and resistance) and RAM) and reference) and (sense adj amplifier)	USPAT; EPO; JPO; DERWENT; USOCR	2002/12/04 13:13
3	152	((magnetoresistive and resistance) and RAM) and reference	USPAT; EPO; JPO; DERWENT; USOCR	2002/12/04 13:21
5	4	((magnetoresistive and resistance) and RAM) and precharge	USPAT; EPO; JPO; DERWENT; USOCR	2002/12/04 13:23
6	643	resistance adj memory	USPAT; EPO; JPO; DERWENT; USOCR	2002/12/04 13:35
7	450	(resistance adj memory) and reference	USPAT; EPO; JPO; DERWENT; USOCR	2002/12/04 13:36
8	0	((resistance adj memory) and reference) and chalcogenide	USPAT; EPO; JPO; DERWENT; USOCR	2002/12/04 13:36
9	4910	((resistance adj memory) and reference) chalcogenide	USPAT; EPO; JPO; DERWENT; USOCR	2002/12/04 13:36
10	28	((resistance adj memory) and reference) and chalcogenide	USPAT; EPO; JPO; DERWENT; USOCR	2002/12/04 13:38
11	42	((resistance adj memory) and reference) and precharge	USPAT; EPO; JPO; DERWENT; USOCR	2002/12/04 13:46
12	35	((resistance adj memory) and reference) and refresh	USPAT; EPO; JPO; DERWENT; USOCR	2002/12/04 13:46

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4	16	((magnetoresistive and resistance) and RAM) and reference) and (sense adj amplifier)	USPAT; EPO; JPO; DERWENT; USOCR	2002/12/04 13:13
3	152	((magnetoresistive and resistance) and RAM) and reference	USPAT; EPO; JPO; DERWENT; USOCR	2002/12/04 13:21
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